

XP-002212231

AN - 2001-053501 [07]

AP - JP19990085182 19990329

CPY - NIHA

DC - L03 M26

FS - CPI

IC - C22C14/00 ; C22C21/00 ; C23C14/34

MC - L04-D02 M26-B09 M26-B09C M26-B09N M26-B09P M26-B09S M26-B09X

PA - (NIHA) JAPAN ENERGY CORP

PN - JP2000273623 A 20001003 DW200107 C23C14/34 005pp

PR - JP19990085182 19990329

XA - C2001-015256

XIC - C22C-014/00 ; C22C-021/00 ; C23C-014/34

AB - JP2000273623 NOVELTY - A sputtering target contains 5-65 weight% of aluminum, (in ppm) radioactive elements such as uranium and thorium (0.001), alkali metals such as sodium and potassium (0.1), transition metals such as iron (10), nickel (5), cobalt (2) and chromium (2), and other impurities. The sputtering target has purity of 99.995%.

- USE - For formation of barrier film useful for semiconductor device.

- ADVANTAGE - The sputtering target provides a precise film and reduces the generation of pollution substance from the barrier film. The barrier film inhibits the generation of interface state and joining leak by mixing of metal oxide semiconductor (MOS) on radiation and degradation of MOS boundary surface by alkali metal.

- (Dwg.0/0)

IW - TITANIUM ALLOY SPUTTER TARGET USEFUL BARRIER FILM FORMATION SPECIFIC PURE CONTAIN PRESET AMOUNT URANIUM THORIUM SODIUM POTASSIUM IRON NICKEL COBALT CHROMIUM

IKW - TITANIUM ALLOY SPUTTER TARGET USEFUL BARRIER FILM FORMATION SPECIFIC PURE CONTAIN PRESET AMOUNT URANIUM THORIUM SODIUM POTASSIUM IRON NICKEL COBALT CHROMIUM

NC - 001

OPD - 1999-03-29

ORD - 2000-10-03

PAW - (NIHA) JAPAN ENERGY CORP

TI - Titanium-aluminum alloy sputtering target useful for barrier film formation has specific purity and contains preset amounts of aluminum, uranium and thorium, sodium and potassium, iron, nickel, cobalt and chromium